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Structure	Silicon Monolithic Bipolar IC
Appearance	SIL-9 Pin Plastic Package (Power Type with Fin)
Application	Low Frequency Amplifier
Function	BTL 4.0W x 1ch Power Amplifier with Standby Function and Volume Function

A	Absolute Maximum Ratings				
No.	Item	Symbol	Ratings	Unit	Note
1	Storage Temperature	Tstg	-55 ~ +150	°C	1
2	Operating Ambient Temperature	Topr	-25 ~ +70	°C	1
3	Operating Ambient Pressure	Popr	1.013x10 ⁵ ±0.61x10 ⁵ (1.0±0.6)	Pa (atm)	
4	Operating Constant Acceleration	Gopr	9,810 (1000)	m/s ² (G)	
5	Operating Shock	Sopr	4,900 (500)	m/s ² (G)	
6	Supply Voltage	Vcc	14.4	V	2
7	Supply Current	Icc	1.0	A	
8	Power Dissipation	P _D	1.22	W	Ta=70°C

Operating Supply Voltage Range	Vcc	3.5V ~ 13.5V
--------------------------------	-----	--------------

- Note 1) The temperature of all items shall be Ta=25°C except storage temperature and operating ambient temperature.
 - 2) At no signal input.

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В	Electrical Characteristics (Unless otherwise specified, the ambient temperature is $25^{\circ}\text{C}\pm2^{\circ}\text{C}$, $Vcc=8.0V$, frequency=1kHz and $RL=8\Omega$.)								
N.T.	T.	G 1 1	Test		Limits				NT.
No	Item	Symbol	Cir- cuit	Conditions	min	typ	max	Unit	Note
1	Quiescent Circuit Current	I_{CQ}	1	Vin=0V, Vol=0V	-	20	60	mA	
2	Standby Current	I _{STB}	1	Vin=0V, Vol=0V	-	1	10	μΑ	
3	Output Noise Voltage	V _{NO}	1	Rg=10kΩ, Vol=0V	-	0.10	0.4	mVrms	1
4	Voltage Gain	Gv	1	Po=0.5W, Vol=1.25V	31	33	35	dB	
5	Total Harmonic Distortion	THD	1	Po=0.5W, Vol=1.25V	-	0.10	0.5	%	
6	Maximum Power Output 1	Po1	1	THD=10%, Vol=1.25V	2.4	3.0	-	W	
7	Maximum Power Output 2	Po2	1	Vcc=9V THD=10%, Vol=1.25V	3.2	4.0	-	W	
8	Ripple Rejection Ratio	RR	1	Rg=10kΩ, Vol=0V Vr=0.5Vrms, fr=120Hz	30	50	-	dB	1
9	Output Offset Voltage	Voff	1	Rg=10kΩ, Vol=0V	-250	0	250	mV	
10	Volume Attenuation Ratio	Att	1	Po=0.5W, Vol=0V	70	85	-	dB	1
11	Middle Voltage Gain	Gvm	1	Po=0.5W, Vol=0.6V	20.5	23.5	26.5	dB	

Note 1) For this measurement, use the BPF = 15Hz ~ 30 kHz (12dB/OCT).

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Product Specifications (Reference Data for Design) AN7523N

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В	Electrical Characteristics (Unless otherwise specified, the ambient temperature is 25°C±2°C, Vcc=8.0V, frequency=1kHz and RL=8Ω.)				·2°C,				
No	Item	Symbol	Test		Limits		Unit	Note	
110				min	typ	max	Uiilt	Note	
1	Standby pin current	I _{STB2}	1	Vin=0V, Vstb=3V	-	-	25	μΑ	
2	Volume pin current	I _{VOL}	1	Vin=0V, Vol=0V	-12	-	-	μΑ	
3	Input Impedance	Zi	1	Vin=±0.3VDC	24	30	36	kΩ	

Note) The above characteristics are reference values determined for IC design, but not guaranteed values for shipping inspection. If problems were to occur, counter measures will be sincerely discussed.

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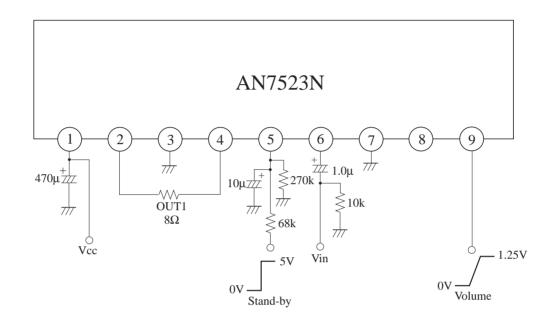
Product Specifications

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(Description of test circuit and test method)

Test Circuit 1



Note) If the standby pin is open or 0V, the IC is on standby state.

The IC is in the state of volume minimum if the Volume pin is ground.

The IC is in the state of volume maximum if the Volume pin is open.

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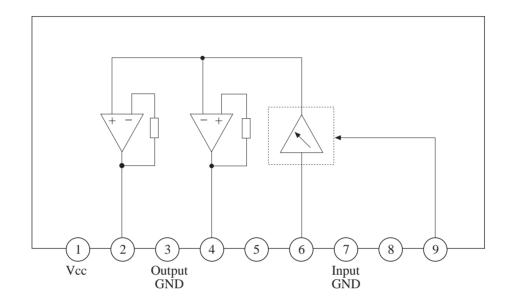
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Circuit Function Block Diagram



Pin Descriptions

Pin No.	Description	
1	Vcc	
2	Ch Output (+)	
3	GND (Output)	
4	Ch Output (-)	
5	Standby	
6	Ch Input	
7	GND (Input)	
8	N.C	
9	Volume	

Note) Do not apply voltage or current to NC pin from outside.

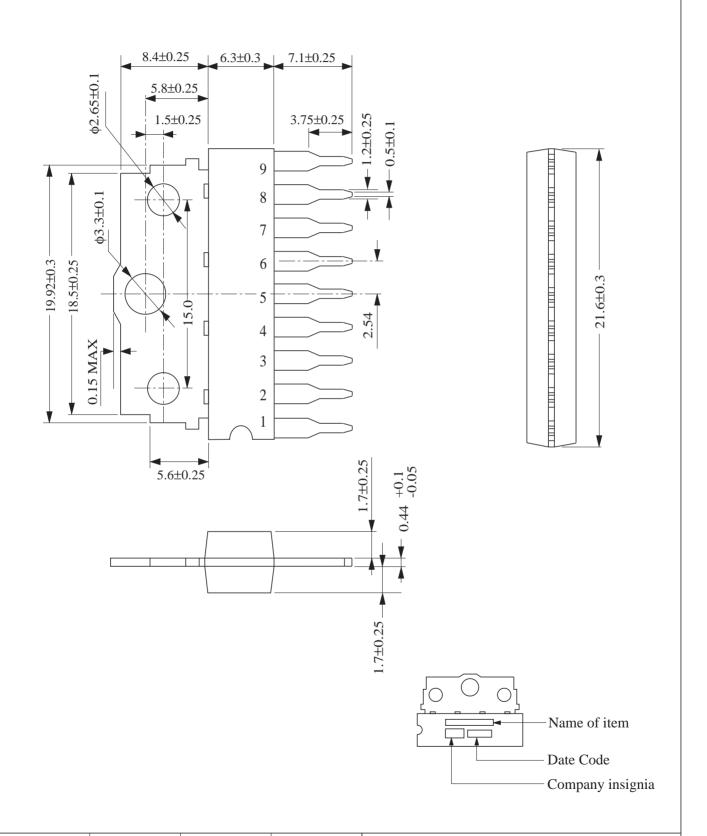
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Package Name

F - 9S

Unit: mm



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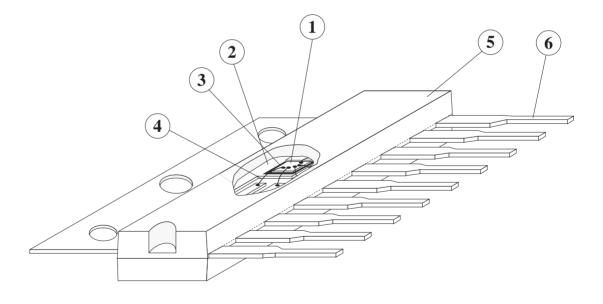
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(Structure Description)

Chip surface passivation	SiN,	PSG,	Others ()	1
Lead frame material	Fe group,	Cu group,	Others ()	2,6
Inner lead surface process	Ag plating,	Au plating,	Others ()	2
Outer lead surface process	Solder plating,	Solder dip,	Others ()	6
Chip mounting method	Ag paste,	Au-Si alloy, Solder,	Others ()	3
Wire bonding method	Thermalsonic bo	onding,	Others ()	4
Wire material, Diameter	Au,	Diameter 30 μm	Others ()	4
Mold material	Epoxy,		Others ()	5
Molding method	Transfer mold,	Multiplunger mold,	Others ()	5

Package 9-SIP(F)



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Product Specifications (Technical Data)

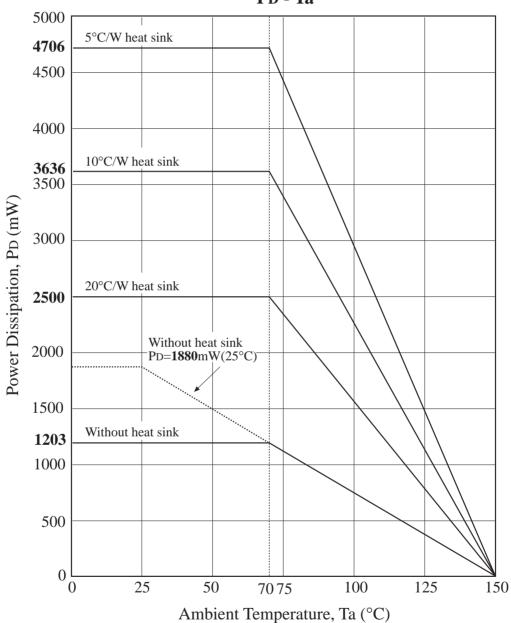
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$$\begin{pmatrix}
Rth(j-c) = 12.0^{\circ}C/W \\
Rth(j-a) = 66.5^{\circ}C/W
\end{pmatrix}$$

F-9S Package Power Dissipation





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(Precautions for use)

- 1) Make sure that the IC is free of any pin short-circuiting, ground short, and load short-circuiting.
- 2) Ground the radiation fin so that there will be no difference in electric potential between the radiation fin and ground.
- 3) The thermal protection circuit operates at a Tj of approximately 150°C. The thermal protection circuit is reset automatically when the temperature drops.
- 4) Make sure that the heat radiation design is effective enough if the Vcc is comparatively high or the IC operates high output power.
- 5) Connect only ground pin for signal sources to the signal GND pin of the amplifier on the previous stage.
- 6) The electric surge voltage for this IC low, therefore be extra careful when using the following pin (at 200pF): Pin 6=+180V, Pin 9=+100V

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